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Automotive N-Channel 40 V (D-S) 175 °C MOSFET

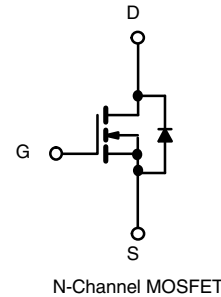
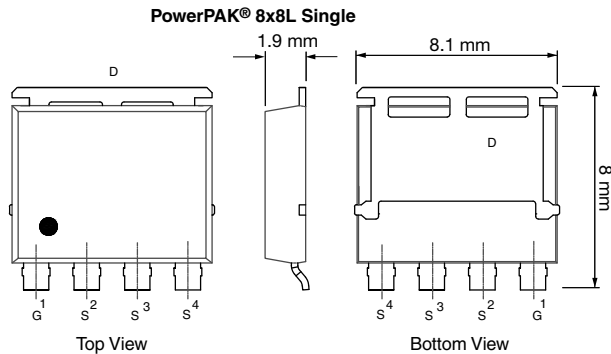
 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0017
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0020
I_D (A)	200
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.9 mm height
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	PowerPAK 8x8L
Lead (Pb)-free and Halogen-free	SQJQ402E-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C ^a	200
		$T_C = 125$ °C	127
Continuous Source Current (Diode Conduction)	I_S	200	A
Pulsed Drain Current ^b	I_{DM}	300	
Single Pulse Avalanche Current	I_{AS}	L = 0.1 mH	85
Single Pulse Avalanche Energy			E_{AS}
Maximum Power Dissipation	P_D	$T_C = 25$ °C	150
		$T_C = 125$ °C	50
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)			

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square Pcb (Fr4 material).
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 8x8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	100	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A	-	0.0013	0.0017	Ω
		V _{GS} = 4.5 V	I _D = 10 A	-	0.0015	0.0020	
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0026	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0031	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A		-	140	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	-	10 760	13 500	pF
Output Capacitance	C _{oss}			-	1370	1800	
Reverse Transfer Capacitance	C _{rss}			-	650	850	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 40 A	-	169	260	nC
Gate-Source Charge ^c	Q _{gs}			-	32	-	
Gate-Drain Charge ^c	Q _{gd}			-	29	-	
Gate Resistance	R _g	f = 1 MHz		0.6	1.3	2.5	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 0.5 Ω I _D ≅ 40 A, V _{GEN} = 10 V, R _g = 1 Ω		-	19	30	ns
Rise Time ^c	t _r			-	15	25	
Turn-Off Delay Time ^c	t _{d(off)}			-	69	110	
Fall Time ^c	t _f			-	11	20	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	300	A
Forward Voltage	V _{SD}	I _F = 50 A, V _{GS} = 0		-	0.82	1.2	V

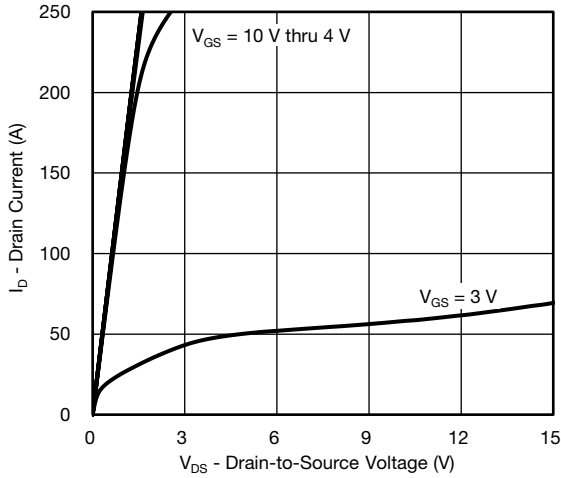
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

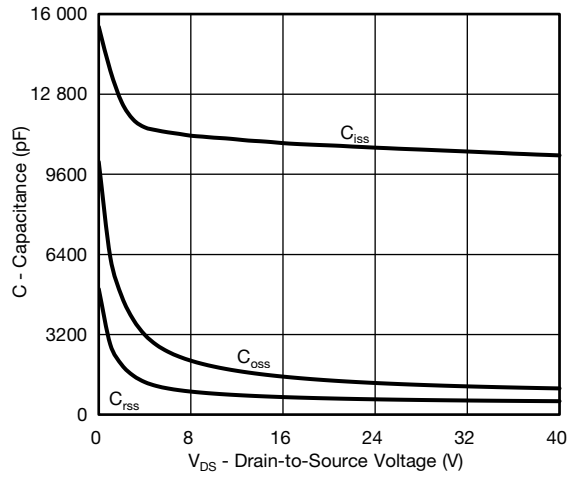
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



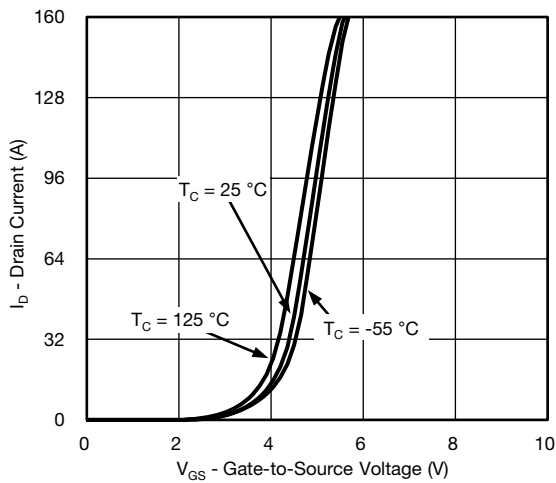
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



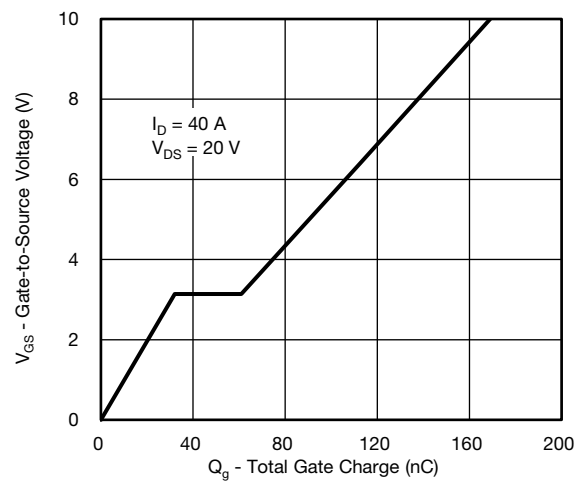
Output Characteristics



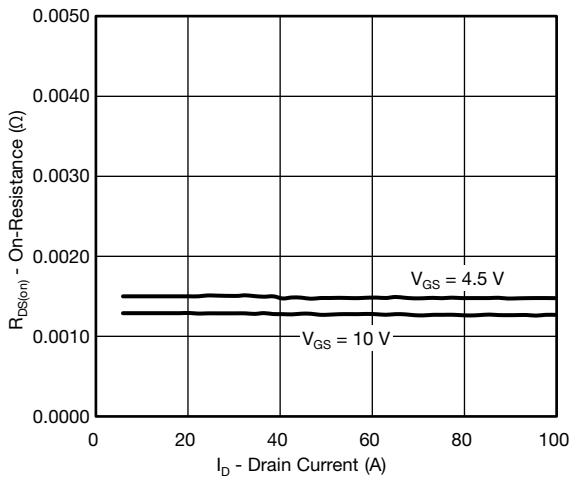
Capacitance



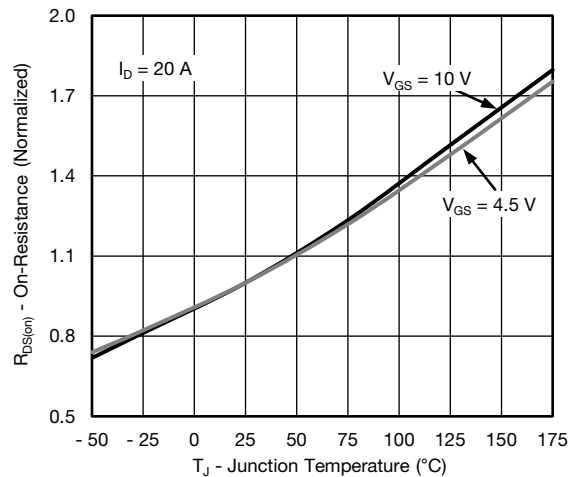
Transfer Characteristics



Gate Charge



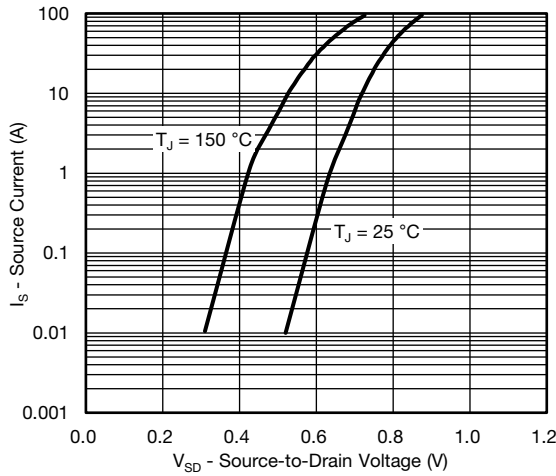
On-Resistance vs. Drain Current



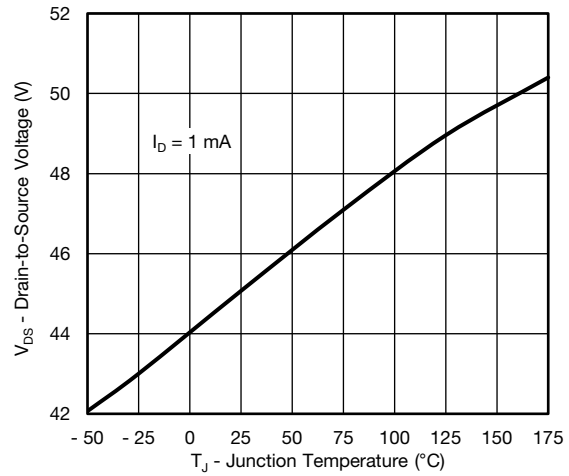
On-Resistance vs. Junction Temperature



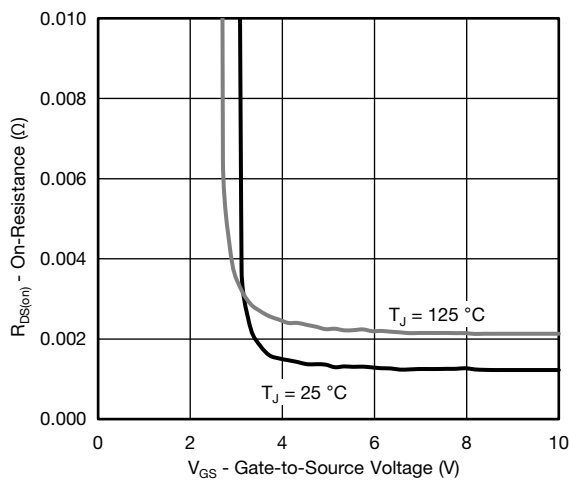
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



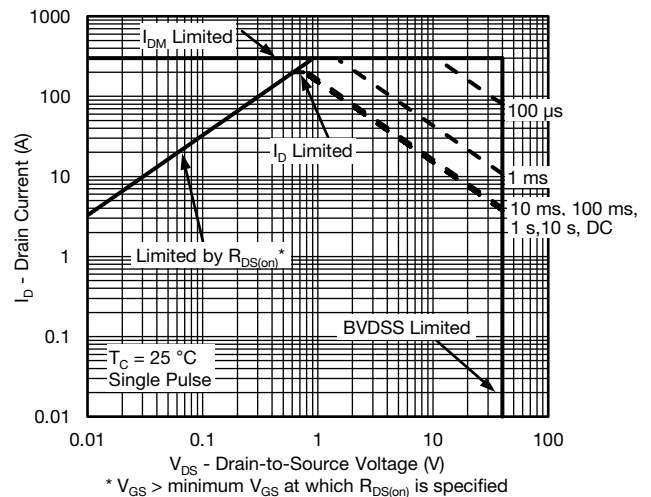
Source Drain Diode Forward Voltage



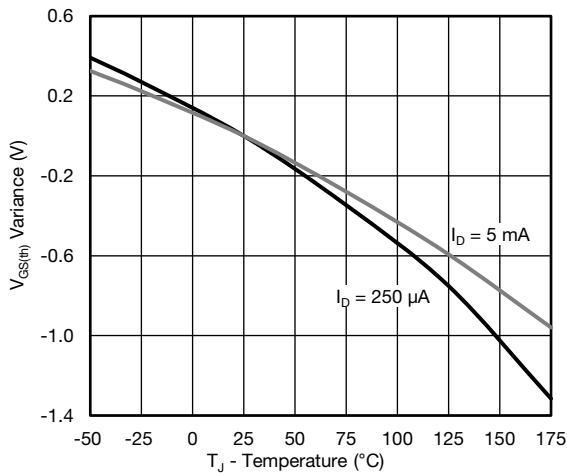
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



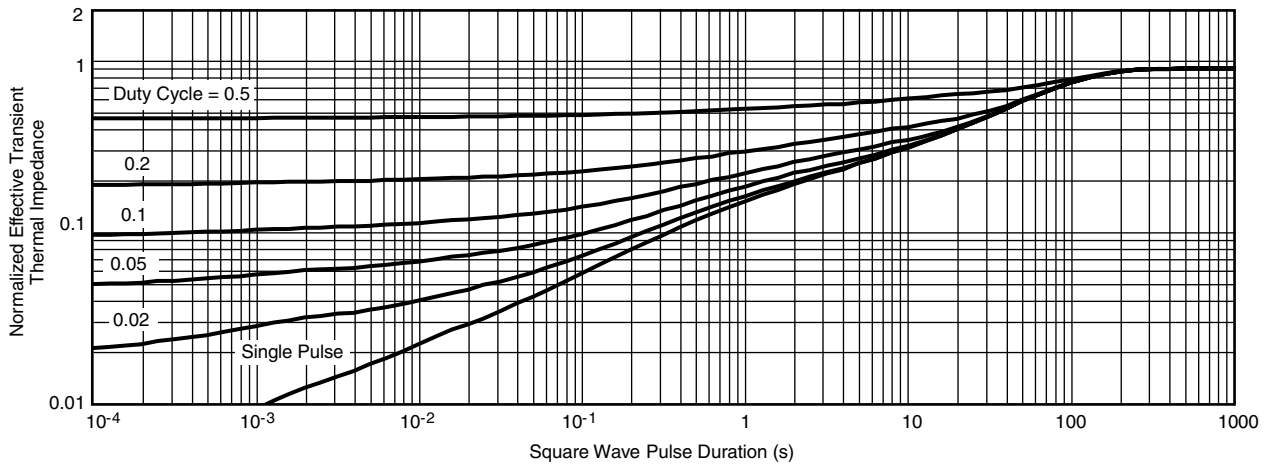
Safe Operating Area



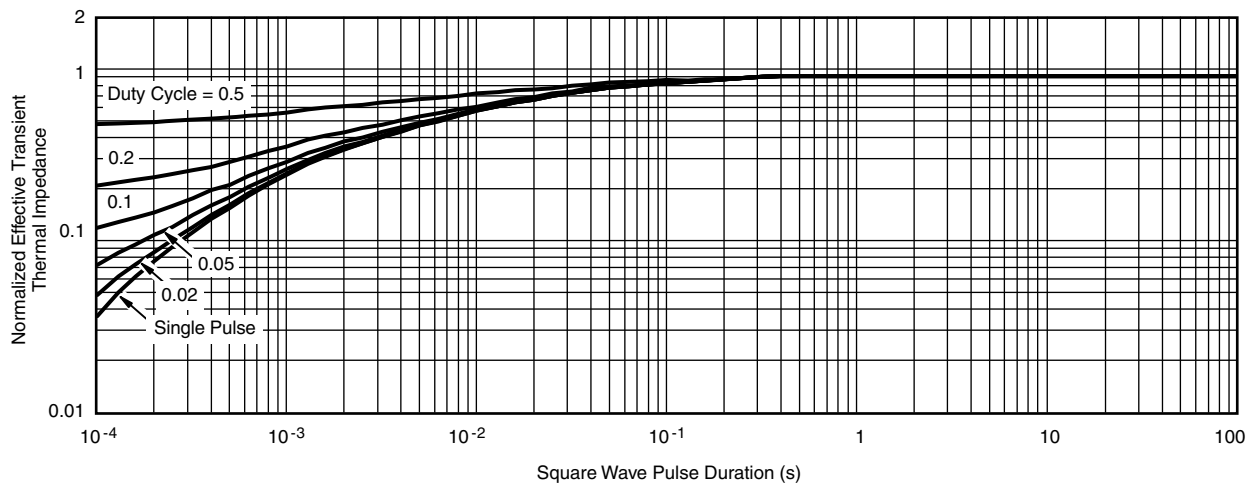
Threshold Voltage



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

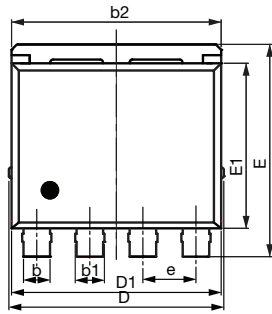


Normalized Thermal Transient Impedance, Junction-to-Case

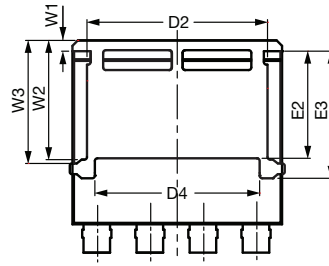
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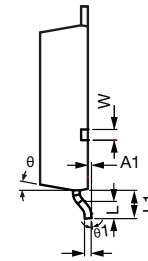
PowerPAK[®] 8 x 8L Case Outline



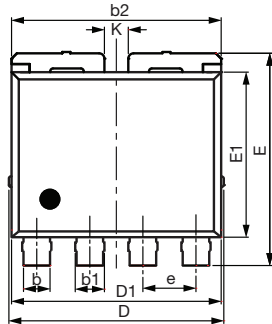
Top view (single)



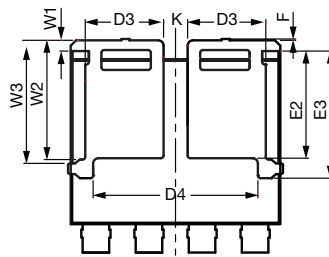
Bottom view (single)



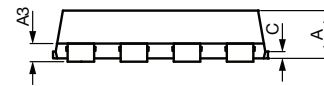
0.25 gauge line



Top view (dual)



Bottom view (dual)

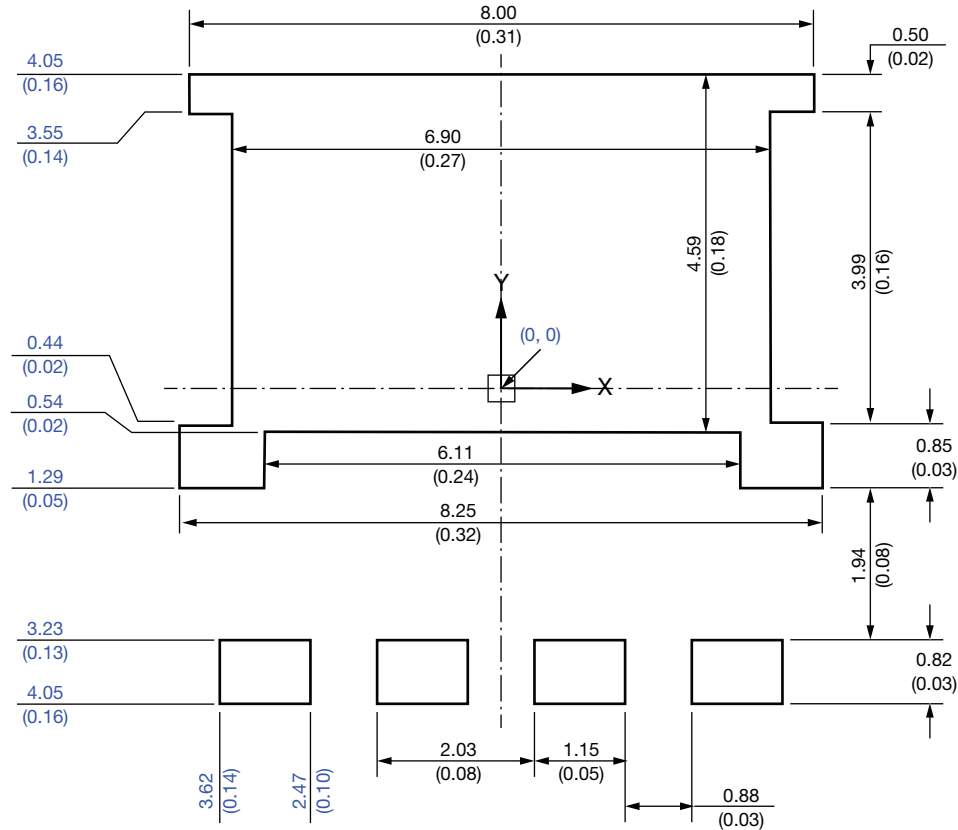


DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
c	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
e	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
F	0.05	0.10	0.15	0.002	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
θ	6°	10°	14°	6°	10°	14°
θ1	0°	3°	8°	0°	3°	8°

C14-0891-Rev. A, 06-Oct-14
DWG: 6026



Recommended Minimum PADS for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

- Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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